

Accepted Manuscript

First principles investigation of the structural and electronic properties of (110), (110) and (111) growth axis AlN/GaN superlattices

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PII: S0577-9073(17)30206-X
DOI: [10.1016/j.cjph.2017.06.004](https://doi.org/10.1016/j.cjph.2017.06.004)
Reference: CJPH 280



To appear in: *Chinese Journal of Physics*

Received date: 2 March 2017
Revised date: 27 May 2017
Accepted date: 3 June 2017

Please cite this article as: Noureddine Mehnane , Nabila Oukli , Mimouna Oukli , First principles investigation of the structural and electronic properties of (110), (110) and (111) growth axis AlN/GaN superlattices, *Chinese Journal of Physics* (2017), doi: [10.1016/j.cjph.2017.06.004](https://doi.org/10.1016/j.cjph.2017.06.004)

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Highlights

- We have calculated the electronic properties of AlN and GaN zinc-blende/zinc-blende superlattices (SLs).
- We have calculated the band structures of the (001), (110) and (111) growth axis SLs with n varying between 1 and 3.
- The most important results are that all these systems exhibit either a direct or indirect bandgap.
- The partial density of states for the three directions are calculated.
- A larger influence of sp and pd coupling between the Ga and N atoms explains the nature of the gaps.

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